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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	280
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe1500-1fgg484

Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based ProASIC3E FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Flash-based ProASIC3E devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based ProASIC3E devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs that are used for these purposes in a system. In addition, glitches and brownouts in system power will not corrupt the ProASIC3E device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based ProASIC3E devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

Firm Errors

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of ProASIC3E flash-based FPGAs. Once it is programmed, the flash cell configuration element of ProASIC3E FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Low Power

Flash-based ProASIC3E devices exhibit power characteristics similar to an ASIC, making them an ideal choice for power-sensitive applications. ProASIC3E devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

ProASIC3E devices also have low dynamic power consumption to further maximize power savings.

Advanced Flash Technology

The ProASIC3E family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

Pro I/Os with Advanced I/O Standards

The ProASIC3E family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). ProASIC3E FPGAs support 19 different I/O standards, including single-ended, differential, and voltage-referenced. The I/Os are organized into banks, with eight banks per device (two per side). The configuration of these banks determines the I/O standards supported. Each I/O bank is subdivided into VREF minibanks, which are used by voltage-referenced I/Os. VREF minibanks contain 8 to 18 I/Os. All the I/Os in a given minibank share a common VREF line. Therefore, if any I/O in a given VREF minibank is configured as a VREF pin, the remaining I/Os in that minibank will be able to use that reference voltage.

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications (e.g., PCI 66 MHz, bidirectional SSTL 2 and 3, Class I and II)
- Double-Data-Rate applications (e.g., DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications, and DDR 200 MHz SRAM using bidirectional HSTL Class II)

ProASIC3E banks support M-LVDS with 20 multi-drop points.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User's Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-3 on page 1-7).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

   1 – I/O is set to drive out logic High

   0 – I/O is set to drive out logic Low

   Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

   Z -Tri-State: I/O is tristated

Table 2-9 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings (continued) (continued)[1]

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
SSTL3 (I)	30	3.3	26.02	114.87
SSTL3 (II)	30	3.3	42.21	131.76
Differential				
LVDS/B-LVDS/M-LVDS	–	2.5	7.70	89.62
LVPECL	–	3.3	19.42	168.02

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *PDC3 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCC and VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Power Consumption of Various Internal Resources

Table 2-10 • Different Components Contributing to the Dynamic Power Consumption in ProASIC3E Devices

Parameter	Definition	Device-Specific Dynamic Contributions (µW/MHz)		
		A3PE600	A3PE1500	A3PE3000
PAC1	Clock contribution of a Global Rib	12.77	16.21	19.7
PAC2	Clock contribution of a Global Spine	1.85	3.06	4.16
PAC3	Clock contribution of a VersaTile row	0.88		
PAC4	Clock contribution of a VersaTile used as a sequential module	0.12		
PAC5	First contribution of a VersaTile used as a sequential module	0.07		
PAC6	Second contribution of a VersaTile used as a sequential module	0.29		
PAC7	Contribution of a VersaTile used as a combinatorial module	0.29		
PAC8	Average contribution of a routing net	0.70		
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-8 on page 2-6.		
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-9 on page 2-7		
PAC11	Average contribution of a RAM block during a read operation	25.00		
PAC12	Average contribution of a RAM block during a write operation	30.00		
PAC13	Static PLL contribution	2.55 mW		
PAC14	Dynamic contribution for PLL	2.60		

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power calculator or SmartPower in Libero SoC.

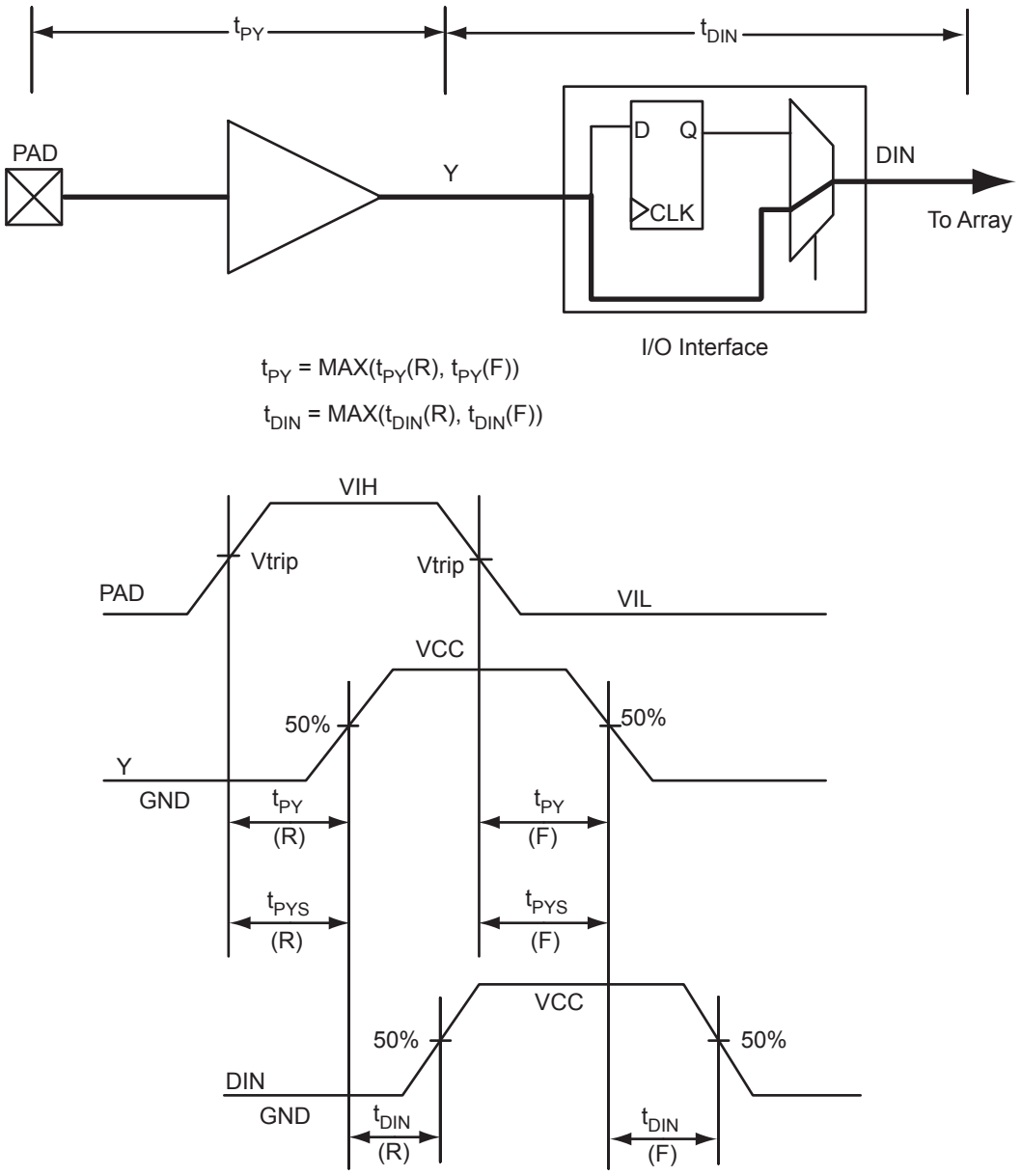


Figure 2-3 • **Input Buffer Timing Model and Delays (example)**

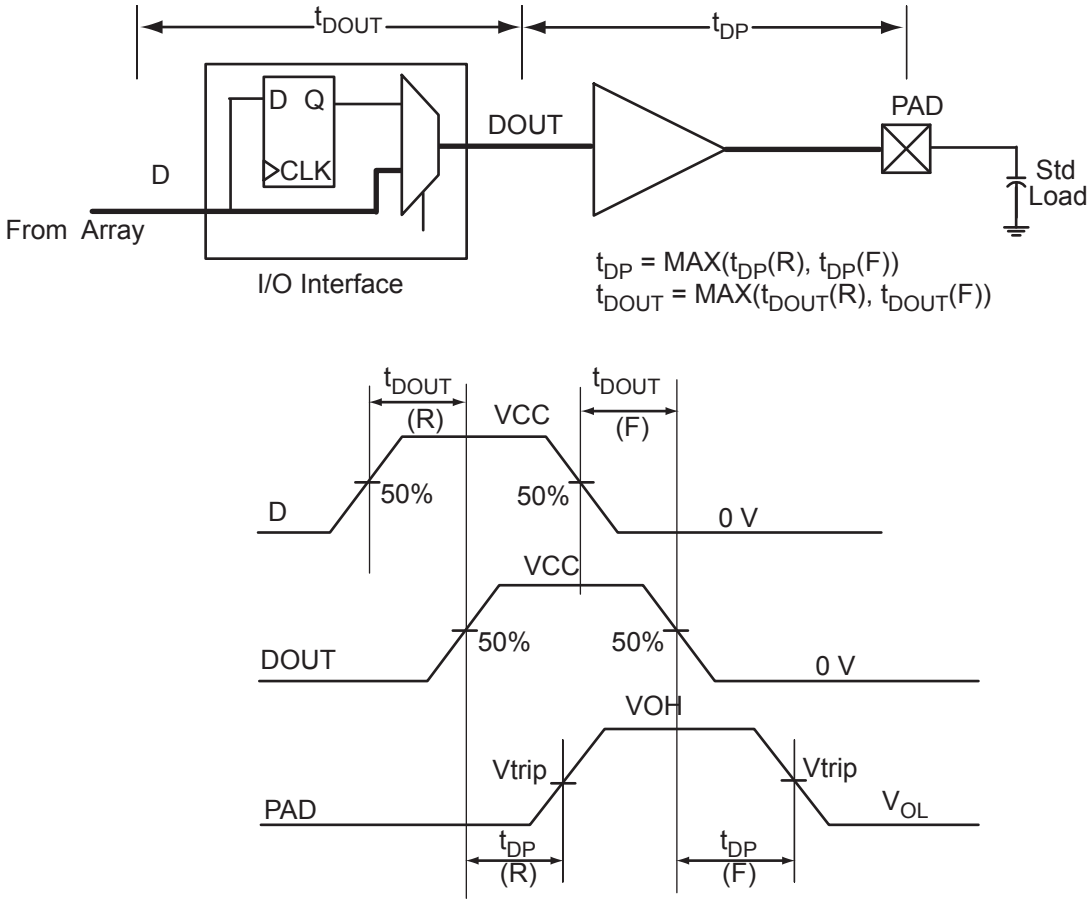


Figure 2-4 • **Output Buffer Model and Delays (example)**

Timing Characteristics

Table 2-43 • 1.5 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	8.53	0.04	1.70	2.14	0.43	7.26	8.53	3.39	2.79	9.50	10.77	ns
	–1	0.56	7.26	0.04	1.44	1.82	0.36	6.18	7.26	2.89	2.37	8.08	9.16	ns
	–2	0.49	6.37	0.03	1.27	1.60	0.32	5.42	6.37	2.53	2.08	7.09	8.04	ns
4 mA	Std.	0.66	5.41	0.04	1.70	2.14	0.43	5.22	5.41	3.75	3.48	7.45	7.65	ns
	–1	0.56	4.60	0.04	1.44	1.82	0.36	4.44	4.60	3.19	2.96	6.34	6.50	ns
	–2	0.49	4.04	0.03	1.27	1.60	0.32	3.89	4.04	2.80	2.60	5.56	5.71	ns
6 mA	Std.	0.66	4.80	0.04	1.70	2.14	0.43	4.89	4.75	3.83	3.67	7.13	6.98	ns
	–1	0.56	4.09	0.04	1.44	1.82	0.36	4.16	4.04	3.26	3.12	6.06	5.94	ns
	–2	0.49	3.59	0.03	1.27	1.60	0.32	3.65	3.54	2.86	2.74	5.32	5.21	ns
8 mA	Std.	0.66	4.42	0.04	1.70	2.14	0.43	4.50	3.62	3.96	4.37	6.74	5.86	ns
	–1	0.56	3.76	0.04	1.44	1.82	0.36	3.83	3.08	3.37	3.72	5.73	4.98	ns
	–2	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37	ns
12 mA	Std.	0.66	4.42	0.04	1.70	2.14	0.43	4.50	3.62	3.96	4.37	6.74	5.86	ns
	–1	0.56	3.76	0.04	1.44	1.82	0.36	3.83	3.08	3.37	3.72	5.73	4.98	ns
	–2	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

Table 2-44 • 1.5 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.11	0.04	1.70	2.14	0.43	14.37	13.14	3.40	2.68	16.61	15.37	ns
	–1	0.56	12.00	0.04	1.44	1.82	0.36	12.22	11.17	2.90	2.28	14.13	13.08	ns
	–2	0.49	10.54	0.03	1.27	1.60	0.32	10.73	9.81	2.54	2.00	12.40	11.48	ns
4 mA	Std.	0.66	11.23	0.04	1.70	2.14	0.43	11.44	9.87	3.77	3.36	13.68	12.10	ns
	–1	0.56	9.55	0.04	1.44	1.82	0.36	9.73	8.39	3.21	2.86	11.63	10.29	ns
	–2	0.49	8.39	0.03	1.27	1.60	0.32	8.54	7.37	2.81	2.51	10.21	9.04	ns
6 mA	Std.	0.66	10.45	0.04	1.70	2.14	0.43	10.65	9.24	3.84	3.55	12.88	11.48	ns
	–1	0.56	8.89	0.04	1.44	1.82	0.36	9.06	7.86	3.27	3.02	10.96	9.76	ns
	–2	0.49	7.81	0.03	1.27	1.60	0.32	7.95	6.90	2.87	2.65	9.62	8.57	ns
8 mA	Std.	0.66	10.02	0.04	1.70	2.14	0.43	10.20	9.23	3.97	4.22	12.44	11.47	ns
	–1	0.56	8.52	0.04	1.44	1.82	0.36	8.68	7.85	3.38	3.59	10.58	9.75	ns
	–2	0.49	7.48	0.03	1.27	1.60	0.32	7.62	6.89	2.97	3.15	9.29	8.56	ns
12 mA	Std.	0.66	10.02	0.04	1.70	2.14	0.43	10.20	9.23	3.97	4.22	12.44	11.47	ns
	–1	0.56	8.52	0.04	1.44	1.82	0.36	8.68	7.85	3.38	3.59	10.58	9.75	ns
	–2	0.49	7.48	0.03	1.27	1.60	0.32	7.62	6.89	2.97	3.15	9.29	8.56	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

HSTL Class II

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-63 • Minimum and Maximum DC Input and Output Levels

HSTL Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max., V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
15 mA[3]	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	15	15	55	66	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Output drive strength is below JEDEC specification.*

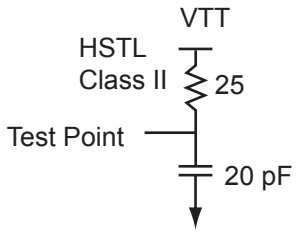


Figure 2-17 • AC Loading

Table 2-64 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.1	VREF + 0.1	0.75	0.75	0.75	20

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-65 • HSTL Class II
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V, VREF = 0.75 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	3.02	0.04	2.12	0.43	3.08	2.71			5.32	4.95	ns
–1	0.56	2.57	0.04	1.81	0.36	2.62	2.31			4.52	4.21	ns
–2	0.49	2.26	0.03	1.59	0.32	2.30	2.03			3.97	3.70	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

***Table 2-84* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

*Note: *See Figure 2-25 on page 2-53 for more information.*

Output DDR Module

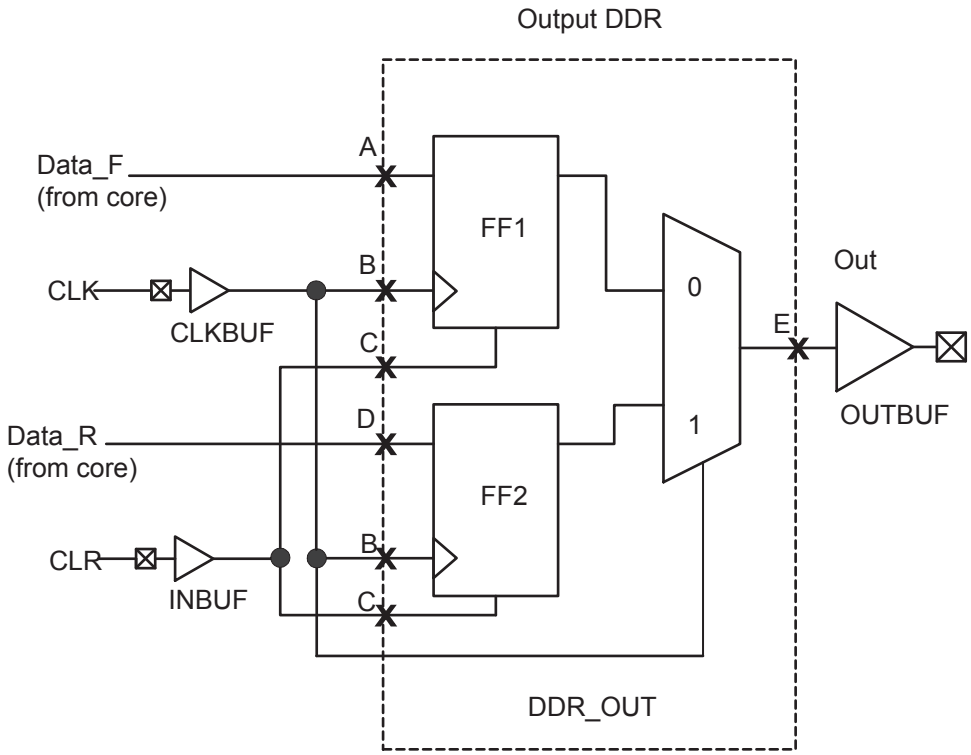


Figure 2-32 • **Output DDR Timing Model**

Table 2-91 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The ProASIC3E library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *Fusion, IGLOO®/e, and ProASIC3/E Macro Library Guide*.

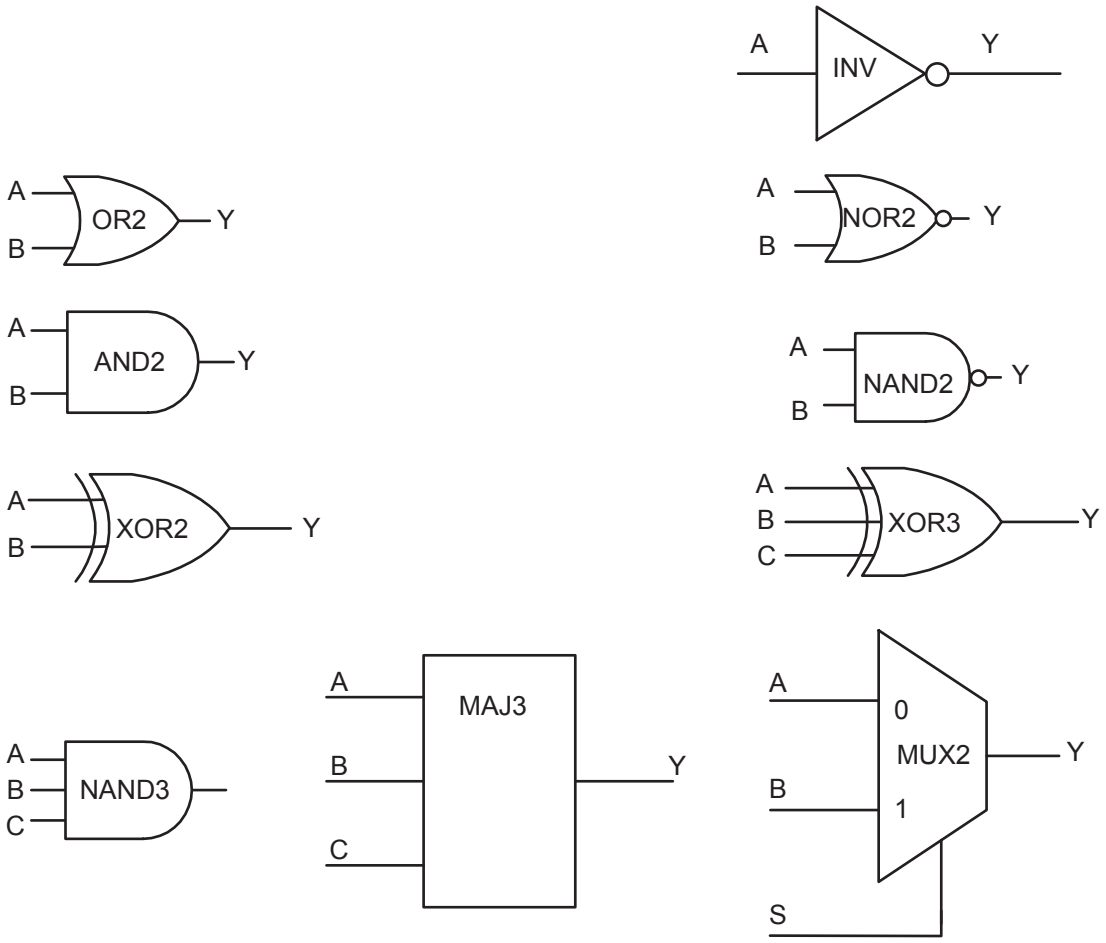
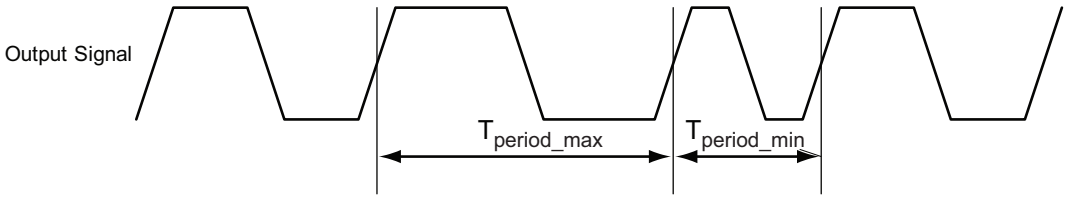


Figure 2-34 • **Sample of Combinatorial Cells**



Note: Peak-to-peak jitter measurements are defined by $T_{peak\text{-}to\text{-}peak} = T_{period\_max} - T_{period\_min}$.

Figure 2-39 • **Peak-to-Peak Jitter Definition**

Timing Waveforms

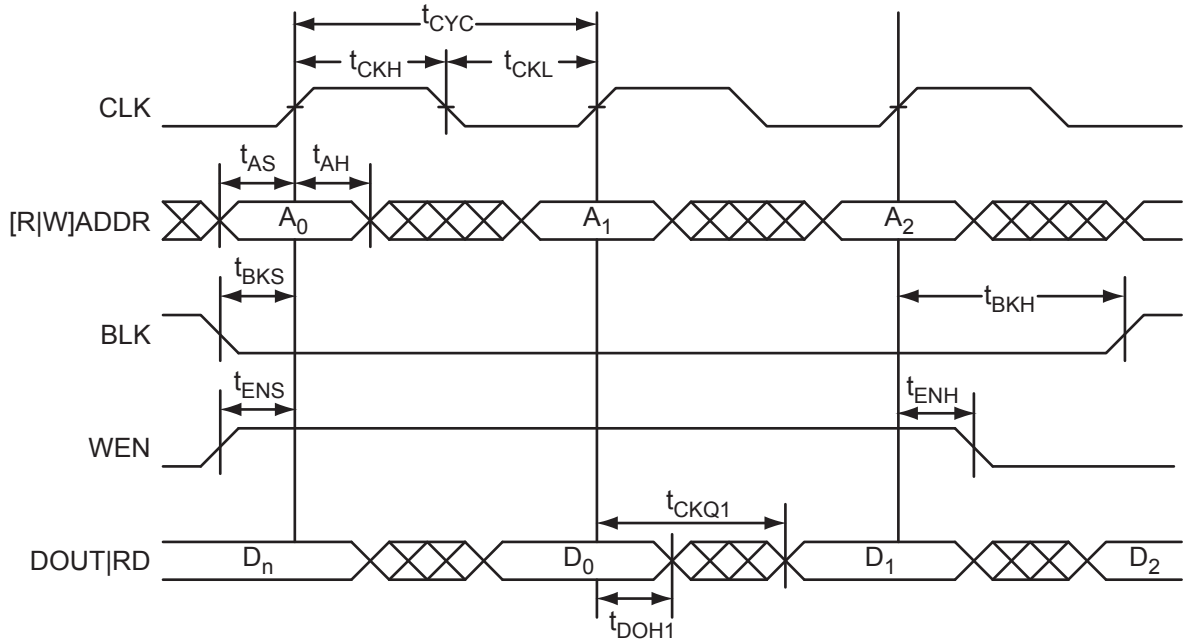


Figure 2-41 • **RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.**

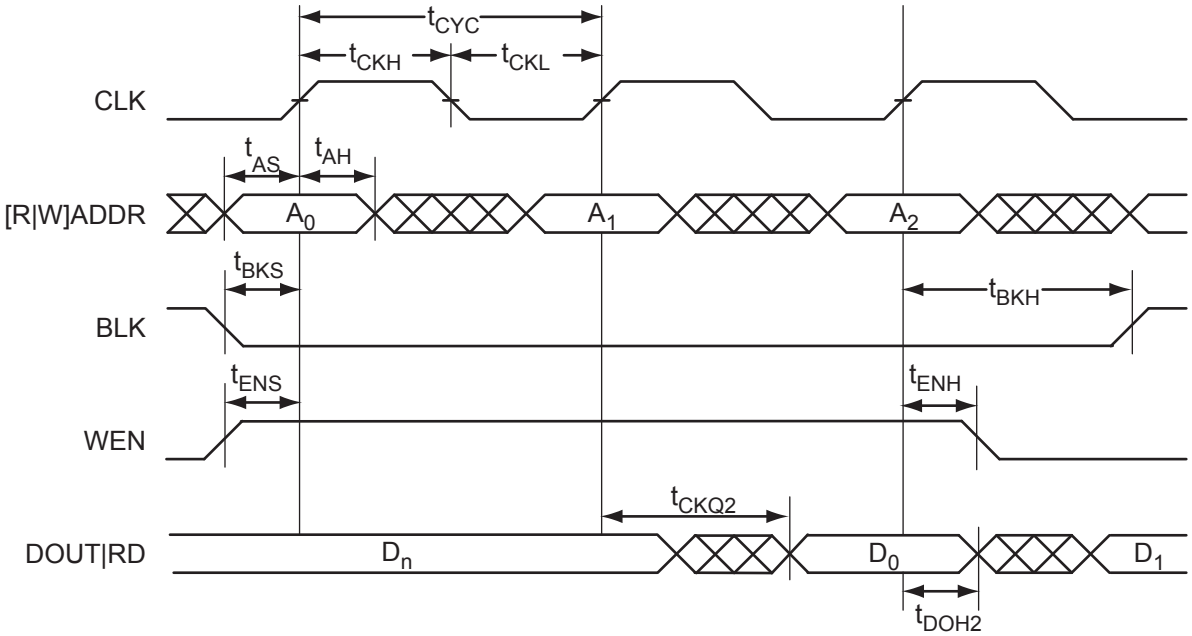


Figure 2-42 • **RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.**

Table 2-100 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.18	0.20	0.24	ns
t_{ENH}	REN, WEN hold time	0.06	0.07	0.08	ns
t_{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t_{C2CRWH} [1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t_{C2CWRH} [1]	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.59	0.50	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

PQ208	
Pin Number	**A3PE600 Function**
1	GND
2	GNDQ
3	VMV7
4	GAB2/IO133PSB7V1
5	GAA2/IO134PDB7V1
6	IO134NDB7V1
7	GAC2/IO132PDB7V1
8	IO132NDB7V1
9	IO130PDB7V1
10	IO130NDB7V1
11	IO127PDB7V1
12	IO127NDB7V1
13	IO126PDB7V0
14	IO126NDB7V0
15	IO124PSB7V0
16	VCC
17	GND
18	VCCIB7
19	IO122PPB7V0
20	IO121PSB7V0
21	IO122NPB7V0
22	GFC1/IO120PSB7V0
23	GFB1/IO119PDB7V0
24	GFB0/IO119NDB7V0
25	VCOMPLF
26	GFA0/IO118NPB6V1
27	VCCPLF
28	GFA1/IO118PPB6V1
29	GND
30	GFA2/IO117PDB6V1
31	IO117NDB6V1
32	GFB2/IO116PPB6V1
33	GFC2/IO115PPB6V1
34	IO116NPB6V1
35	IO115NPB6V1
36	VCC

PQ208	
Pin Number	**A3PE600 Function**
37	IO112PDB6V1
38	IO112NDB6V1
39	IO108PSB6V0
40	VCCIB6
41	GND
42	IO106PDB6V0
43	IO106NDB6V0
44	GEC1/IO104PDB6V0
45	GEC0/IO104NDB6V0
46	GEB1/IO103PPB6V0
47	GEA1/IO102PPB6V0
48	GEB0/IO103NPB6V0
49	GEA0/IO102NPB6V0
50	VMV6
51	GNDQ
52	GND
53	VMV5
54	GNDQ
55	IO101NDB5V2
56	GEA2/IO101PDB5V2
57	IO100NDB5V2
58	GEB2/IO100PDB5V2
59	IO99NDB5V2
60	GEC2/IO99PDB5V2
61	IO98PSB5V2
62	VCCIB5
63	IO96PSB5V2
64	IO94NDB5V1
65	GND
66	IO94PDB5V1
67	IO92NDB5V1
68	IO92PDB5V1
69	IO88NDB5V0
70	IO88PDB5V0
71	VCC

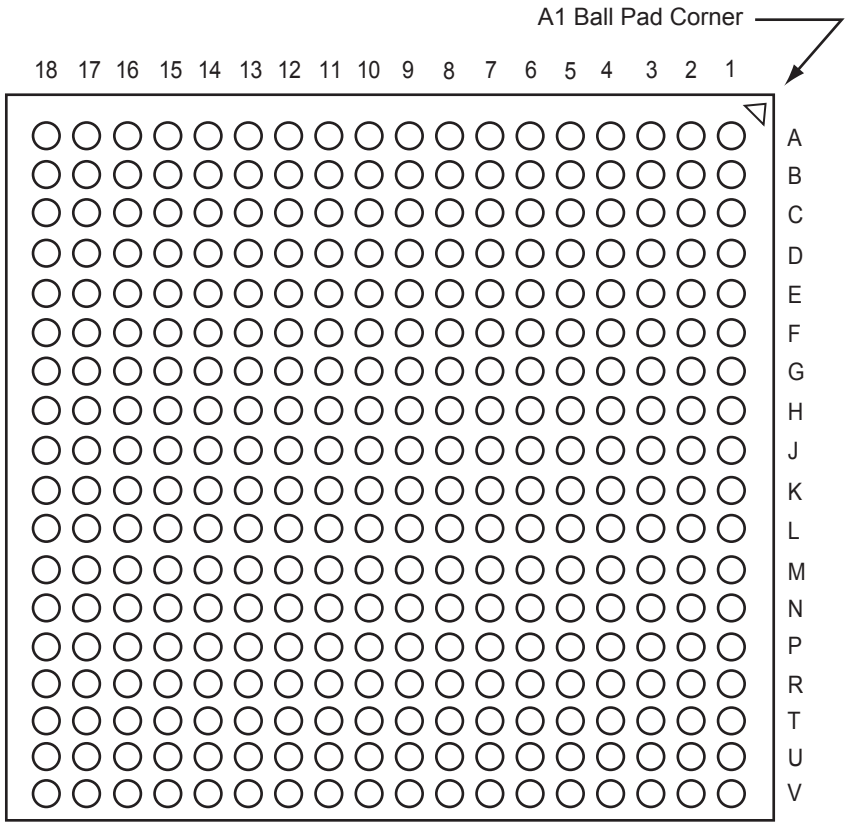
PQ208	
Pin Number	**A3PE600 Function**
72	VCCIB5
73	IO85NPB5V0
74	IO84NPB5V0
75	IO85PPB5V0
76	IO84PPB5V0
77	IO83NPB5V0
78	IO82NPB5V0
79	IO83PPB5V0
80	IO82PPB5V0
81	GND
82	IO80NDB4V1
83	IO80PDB4V1
84	IO79NPB4V1
85	IO78NPB4V1
86	IO79PPB4V1
87	IO78PPB4V1
88	VCC
89	VCCIB4
90	IO76NDB4V1
91	IO76PDB4V1
92	IO72NDB4V0
93	IO72PDB4V0
94	IO70NDB4V0
95	GDC2/IO70PDB4V0
96	IO68NDB4V0
97	GND
98	GDA2/IO68PDB4V0
99	GDB2/IO69PSB4V0
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV4
105	GND
106	VPUMP
107	GNDQ

FG256	
Pin Number	**A3PE600 Function**
G13	GCC1/IO50PPB2V1
G14	IO44NDB2V1
G15	IO44PDB2V1
G16	IO49NSB2V1
H1	GFB0/IO119NPB7V0
H2	GFA0/IO118NDB6V1
H3	GFB1/IO119PPB7V0
H4	VCOMPLF
H5	GFC0/IO120NPB7V0
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO50NPB2V1
H13	GCB1/IO51PPB2V1
H14	GCA0/IO52NPB3V0
H15	VCOMPLC
H16	GCB0/IO51NPB2V1
J1	GFA2/IO117PSB6V1
J2	GFA1/IO118PDB6V1
J3	VCCPLF
J4	IO116NDB6V1
J5	GFB2/IO116PDB6V1
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO54PPB3V0
J13	GCA1/IO52PPB3V0
J14	GCC2/IO55PPB3V0
J15	VCCPLC
J16	GCA2/IO53PSB3V0

FG256	
Pin Number	**A3PE600 Function**
K1	GFC2/IO115PSB6V1
K2	IO113PPB6V1
K3	IO112PDB6V1
K4	IO112NDB6V1
K5	VCCIB6
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB3
K13	IO54NPB3V0
K14	IO57NPB3V0
K15	IO55NPB3V0
K16	IO57PPB3V0
L1	IO113NPB6V1
L2	IO109PPB6V0
L3	IO108PDB6V0
L4	IO108NDB6V0
L5	VCCIB6
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB3
L13	GDB0/IO66NPB3V1
L14	IO60NDB3V1
L15	IO60PDB3V1
L16	IO61PDB3V1
M1	IO109NPB6V0
M2	IO106NDB6V0
M3	IO106PDB6V0
M4	GEC0/IO104NPB6V0

FG256	
Pin Number	**A3PE600 Function**
M5	VMV5
M6	VCCIB5
M7	VCCIB5
M8	IO84NDB5V0
M9	IO84PDB5V0
M10	VCCIB4
M11	VCCIB4
M12	VMV3
M13	VCCPLD
M14	GDB1/IO66PPB3V1
M15	GDC1/IO65PDB3V1
M16	IO61NDB3V1
N1	IO105PDB6V0
N2	IO105NDB6V0
N3	GEC1/IO104PPB6V0
N4	VCOMPLE
N5	GNDQ
N6	GEA2/IO101PPB5V2
N7	IO92NDB5V1
N8	IO90NDB5V1
N9	IO82NDB5V0
N10	IO74NDB4V1
N11	IO74PDB4V1
N12	GNDQ
N13	VCOMPLD
N14	VJTAG
N15	GDC0/IO65NDB3V1
N16	GDA1/IO67PDB3V1
P1	GEB1/IO103PDB6V0
P2	GEB0/IO103NDB6V0
P3	VMV6
P4	VCCPLE
P5	IO101NPB5V2
P6	IO95PPB5V1
P7	IO92PDB5V1
P8	IO90PDB5V1

FG324



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG484	
Pin Number	A3PE1500 Function
A1	GND
A2	GND
A3	VCCIB0
A4	IO05NDB0V0
A5	IO05PDB0V0
A6	IO11NDB0V1
A7	IO11PDB0V1
A8	IO15PDB0V1
A9	IO17PDB0V2
A10	IO27NDB0V3
A11	IO27PDB0V3
A12	IO32PDB1V0
A13	IO43PDB1V1
A14	IO47NDB1V1
A15	IO47PDB1V1
A16	IO51NDB1V2
A17	IO51PDB1V2
A18	IO54NDB1V3
A19	NC
A20	VCCIB1
A21	GND
A22	GND
AA1	GND
AA2	VCCIB6
AA3	NC
AA4	IO161PDB5V3
AA5	IO155NDB5V2
AA6	IO155PDB5V2
AA7	IO154NDB5V2
AA8	IO154PDB5V2
AA9	IO143PDB5V1
AA10	IO143NDB5V1
AA11	IO131PPB4V2
AA12	IO129NDB4V2
AA13	IO129PDB4V2
AA14	NC

FG484	
Pin Number	A3PE1500 Function
AA15	NC
AA16	IO117NDB4V0
AA17	IO117PDB4V0
AA18	IO115NDB4V0
AA19	IO115PDB4V0
AA20	NC
AA21	VCCIB3
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB5
AB4	IO159NDB5V3
AB5	IO159PDB5V3
AB6	IO149NDB5V1
AB7	IO149PDB5V1
AB8	IO138NDB5V0
AB9	IO138PDB5V0
AB10	NC
AB11	NC
AB12	IO127NDB4V2
AB13	IO127PDB4V2
AB14	IO125NDB4V1
AB15	IO125PDB4V1
AB16	IO122NDB4V1
AB17	IO122PDB4V1
AB18	NC
AB19	NC
AB20	VCCIB4
AB21	GND
AB22	GND
B1	GND
B2	VCCIB7
B3	NC
B4	IO03NDB0V0
B5	IO03PDB0V0
B6	IO10NDB0V1

FG484	
Pin Number	A3PE1500 Function
B7	IO10PDB0V1
B8	IO15NDB0V1
B9	IO17NDB0V2
B10	IO20PDB0V2
B11	IO29PDB0V3
B12	IO32NDB1V0
B13	IO43NDB1V1
B14	NC
B15	NC
B16	IO53NDB1V2
B17	IO53PDB1V2
B18	IO54PDB1V3
B19	NC
B20	NC
B21	VCCIB2
B22	GND
C1	VCCIB7
C2	NC
C3	NC
C4	NC
C5	GND
C6	IO07NDB0V0
C7	IO07PDB0V0
C8	VCC
C9	VCC
C10	IO20NDB0V2
C11	IO29NDB0V3
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG484	
Pin Number	**A3PE1500 Function**
V15	IO112NDB4V0
V16	GDB2/IO112PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	IO105NDB3V2
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO165NDB5V3
W6	GEB2/IO165PDB5V3
W7	IO164NDB5V3
W8	IO153NDB5V2
W9	IO153PDB5V2
W10	IO147NDB5V1
W11	IO133NDB4V2
W12	IO130NDB4V2
W13	IO130PDB4V2
W14	IO113NDB4V0
W15	GDC2/IO113PDB4V0
W16	IO111NDB4V0
W17	GDA2/IO111PDB4V0
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB6
Y2	NC
Y3	NC
Y4	IO161NDB5V3
Y5	GND
Y6	IO163NDB5V3

FG484	
Pin Number	**A3PE1500 Function**
Y7	IO163PDB5V3
Y8	VCC
Y9	VCC
Y10	IO147PDB5V1
Y11	IO133PDB4V2
Y12	IO131NPB4V2
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB3

FG896	
Pin Number	A3PE3000 Function
AG9	IO225NPB5V3
AG10	IO223NPB5V3
AG11	IO221PDB5V3
AG12	IO221NDB5V3
AG13	IO205NPB5V1
AG14	IO199NDB5V0
AG15	IO199PDB5V0
AG16	IO187NDB4V4
AG17	IO187PDB4V4
AG18	IO181NDB4V3
AG19	IO171PPB4V2
AG20	IO165NPB4V1
AG21	IO161NPB4V0
AG22	IO159NDB4V0
AG23	IO159PDB4V0
AG24	IO158PPB4V0
AG25	GDB2/IO155PDB4V0
AG26	GDA2/IO154PPB4V0
AG27	GND
AG28	VJTAG
AG29	VCC
AG30	IO149NDB3V4
AH1	GND
AH2	IO233NPB5V4
AH3	VCC
AH4	GEB2/IO232PPB5V4
AH5	VCCIB5
AH6	IO219NDB5V3
AH7	IO219PDB5V3
AH8	IO227NDB5V4
AH9	IO227PDB5V4
AH10	IO225PPB5V3
AH11	IO223PPB5V3
AH12	IO211NDB5V2
AH13	IO211PDB5V2
AH14	IO205PPB5V1

FG896	
Pin Number	A3PE3000 Function
AH15	IO195NDB5V0
AH16	IO185NDB4V3
AH17	IO185PDB4V3
AH18	IO181PDB4V3
AH19	IO177NDB4V2
AH20	IO171NPB4V2
AH21	IO165PPB4V1
AH22	IO161PPB4V0
AH23	IO157NDB4V0
AH24	IO157PDB4V0
AH25	IO155NDB4V0
AH26	VCCIB4
AH27	TDI
AH28	VCC
AH29	VPUMP
AH30	GND
AJ1	GND
AJ2	GND
AJ3	GEA2/IO233PPB5V4
AJ4	VCC
AJ5	IO217NPB5V2
AJ6	VCC
AJ7	IO215NPB5V2
AJ8	IO213NDB5V2
AJ9	IO213PDB5V2
AJ10	IO209NDB5V1
AJ11	IO209PDB5V1
AJ12	IO203NDB5V1
AJ13	IO203PDB5V1
AJ14	IO197NDB5V0
AJ15	IO195PDB5V0
AJ16	IO183NDB4V3
AJ17	IO183PDB4V3
AJ18	IO179NPB4V3
AJ19	IO177PDB4V2
AJ20	IO173NDB4V2

FG896	
Pin Number	A3PE3000 Function
AJ21	IO173PDB4V2
AJ22	IO163NDB4V1
AJ23	IO163PDB4V1
AJ24	IO167NPB4V1
AJ25	VCC
AJ26	IO156NPB4V0
AJ27	VCC
AJ28	TMS
AJ29	GND
AJ30	GND
AK2	GND
AK3	GND
AK4	IO217PPB5V2
AK5	GND
AK6	IO215PPB5V2
AK7	GND
AK8	IO207NDB5V1
AK9	IO207PDB5V1
AK10	IO201NDB5V0
AK11	IO201PDB5V0
AK12	IO193NDB4V4
AK13	IO193PDB4V4
AK14	IO197PDB5V0
AK15	IO191NDB4V4
AK16	IO191PDB4V4
AK17	IO189NDB4V4
AK18	IO189PDB4V4
AK19	IO179PPB4V3
AK20	IO175NDB4V2
AK21	IO175PDB4V2
AK22	IO169NDB4V1
AK23	IO169PDB4V1
AK24	GND
AK25	IO167PPB4V1
AK26	GND
AK27	GDC2/IO156PPB4V0

5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each revision of the ProASIC3E datasheet.

Revision	Changes	Page
Revision 15 (June 2015)	Updated "ProASIC3E Ordering Information". Interchanged the positions of Y- Security Feature and I- Application (Temperature Range) (SAR 67296). Added Note "Only devices with package size greater than or equal to 5x5 are supported". Updated Commercial and Industrial Junction Temperatures (SAR 67588).	*1-III*
	Added the A3PE3000 package to Table 2-5 (SARs 52320 and 58737).	*2-5*
	Updated "VCCIBx I/O Supply Voltage" (SAR 43323).	*3-1*
Revision 14 (May 2014)	Added 2 mA and 6 mA I/O short currents values in *"I/O Short Currents IOSH/IOSL"* (SAR 56295). Added 2 mA and 6 mA minimum and maximum DC input and output levels in "Minimum and Maximum DC Input and Output Levels"(SAR 56295). Added 3.3 V LVTTL / 3.3 V LVCMOS High Slew Commercial-Case Conditions for 2 mA and 6 mA in "3.3 V LVTTL / 3.3 V LVCMOS High Slew" (SAR 56295). Added 3.3 V LVTTL / 3.3 V LVCMOS Low Slew Commercial-Case Conditions for 2 mA and 6 mA in "3.3 V LVTTL / 3.3 V LVCMOS Low Slew" (SAR 56295).	*2-22* *2-24* *2-25* *2-25*
Revision 13 (January 2013)	In the "Features and Benefits" section, updated the Clock Conditioning Circuit (CCC) and PLL Wide Input Frequency Range from '1.5 MHz to 200 MHz' to '1.5MHz to 350 MHz' based on Table 2-98 (SAR 22196).	1-I
	The "ProASIC3E Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43220).	1-III
	Added a note to "Recommended Operating Conditions [1]" table (SAR 42716): The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.	2-2
	The note in "ProASIC3E CCC/PLL Specification" table referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42571).	2-70
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40285). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The "Security" section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1